





P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
001/	$50m\Omega$ @ $V_{GS} = -10V$	-4.5A
-30V	75mΩ @ V _{GS} = -4.5V	-3.7A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- **Power Management Functions**
- **DC-DC Converters**

Features

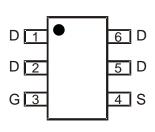
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

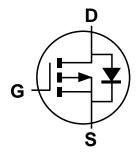
- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.013grams (Approximate)







Device Schematic



Equivalent Circuit

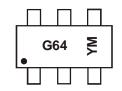
Ordering Information (Note 4)

Part Number		Case	Packaging			
DMP3050LVT-7		TSOT26	3000/Tape & Reel			
Notes:	Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.					

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



G64 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

Year	2011	-	-	2016	2017	20	18	2019	2020	20	21	2022
Code	Υ	-	,	D	Е		F	G	Н		I	J
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	-30	V		
Gate-Source Voltage (Note 5)		V _{GSS}	±25	V	
Continuous Prain Correct (Note C) V 40V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-4.5 -3.5	А
Continuous Drain Current (Note 6) V _{GS} = -10V	t<10s	$T_A = +25$ °C $T_A = +70$ °C	I _D	-5.2 -4.1	А
Maximum Continuous Body Diode Forward Current	Is	-2	Α		
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%	5)	I _{DM}	-25	Α	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	D-	1.6	W	
Total Fower Dissipation (Note 6)	$T_A = +70^{\circ}C$	P_{D}	1.0	VV	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	78		
Thermal Resistance, Junction to Ambient (Note o)	t<10s	$R_{\theta JA}$	49	°C/W	
Thermal Resistance, Junction to Case (Note 6)	Steady State	$R_{ heta JC}$	13		
Operating and Storage Temperature Range		$T_{J_{I}}T_{STG}$	-55 to +150	°C	

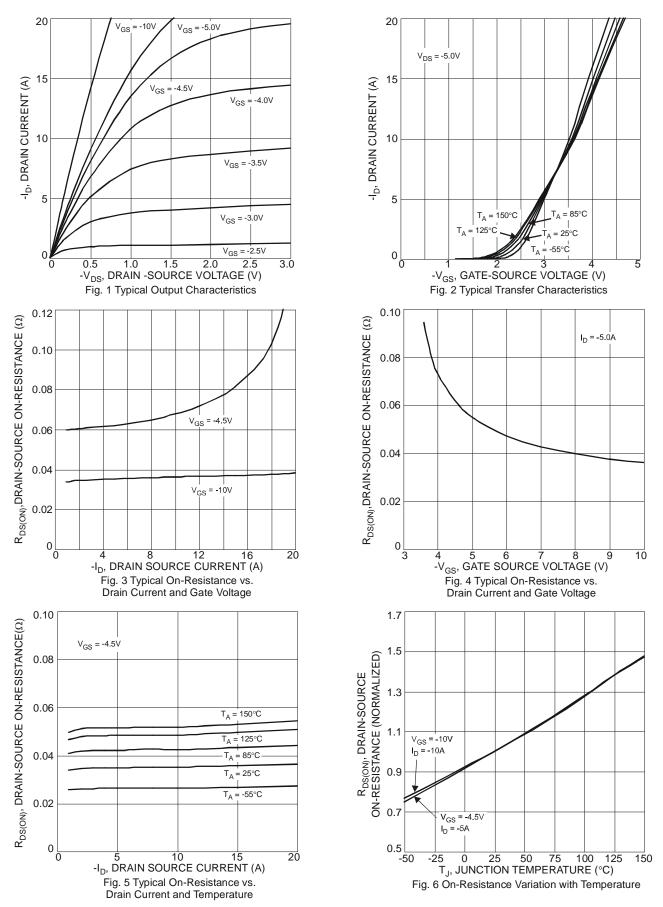
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	-	1	-1	μΑ	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0	-	-2.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	D	-	36	50	mΩ	$V_{GS} = -10V, I_D = -4.5A$	
Static Dialif-Source Off-Resistance	R _{DS(ON)}	-	56	75	1112.2	$V_{GS} = -4.5V, I_D = -3A$	
Forward Transfer Admittance	Y _{fs}	-	7.2	-	S	$V_{DS} = -5V, I_{D} = -5A$	
Diode Forward Voltage	V_{SD}	-	-0.7	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	-	620	-	pF), 45V, V, 0V,	
Output Capacitance	Coss	-	83	-	pF	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	-	62	-	pF	1 = 1.000112	
Gate Resistance	R_{g}	-	10.8	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg	-	5.1	-	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	-	10.5	-	nC	\/ 45\/ L GA	
Gate-Source Charge	Q_{gs}	-	1.8	-	nC	$V_{DS} = -15V, I_{D} = -6A$	
Gate-Drain Charge	Q_{gd}	-	1.9	-	nC	1	
Turn-On Delay Time	t _{D(ON)}	-	6.8	-	ns		
Turn-On Rise Time	t _R	-	4.9	-	ns	$V_{DD} = -15V, V_{GS} = -10V,$	
Turn-Off Delay Time	t _{D(OFF)}	-	28.4	-	ns	$R_g = 6\Omega$, $I_D = -1A$	
Turn-Off Fall Time	t _F	-	12.4	-	ns		

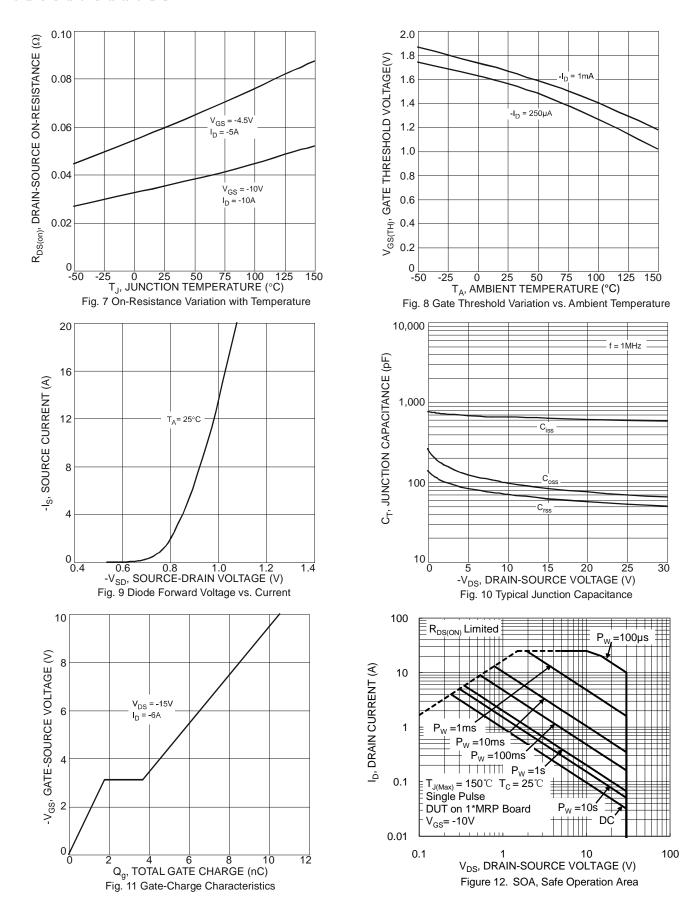
Notes:

- 5. AEC-Q101 V_{GS} maximum is ±20V.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.











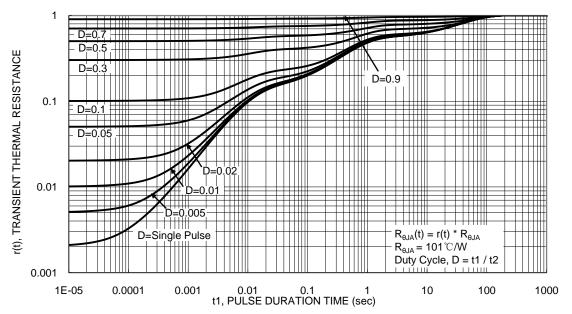


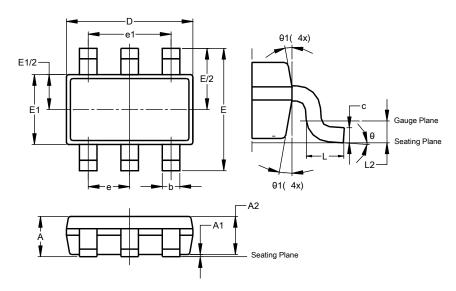
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26

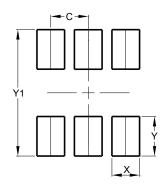


TSOT26								
Dim	Min	Max	Тур					
Α	-	1.00	-					
A1	0.010	0.100	-					
A2	0.840	0.900	-					
D	2.800	3.000	2.900					
Е	2	.800 BS	С					
E1	1.500	1.500 1.700 1.60						
b	0.300	0.300 0.450 -						
C	0.120	0.120 0.200 -						
е	0.950 BSC							
e1	1	.900 BS	С					
L	0.30 0.50 -							
L2	0.250 BSC							
θ	0°	0° 8° 4°						
θ1	4° 12° –							
Δ	All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26



Dimensions	Value (in mm)
С	0.950
Х	0.700
Y	1.000
Y1	3.199



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